

SSM3K7002BFU

High-Speed Switching Applications

Analog Switch Applications

- Small package
- Low ON-resistance : $R_{DS(ON)} = 3.3 \Omega$ (max) (@ $V_{GS} = 4.5 V$)
 : $R_{DS(ON)} = 2.6 \Omega$ (max) (@ $V_{GS} = 5 V$)
 : $R_{DS(ON)} = 2.1 \Omega$ (max) (@ $V_{GS} = 10 V$)

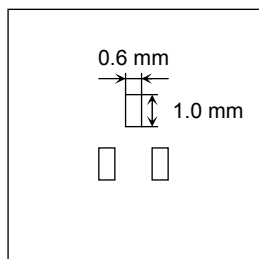
Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	60	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC	I_D	200	mA
	Pulse	I_{DP}	800	
Drain power dissipation (Ta = 25°C)		P_D (Note 1)	150	mW
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	-55 to 150	°C

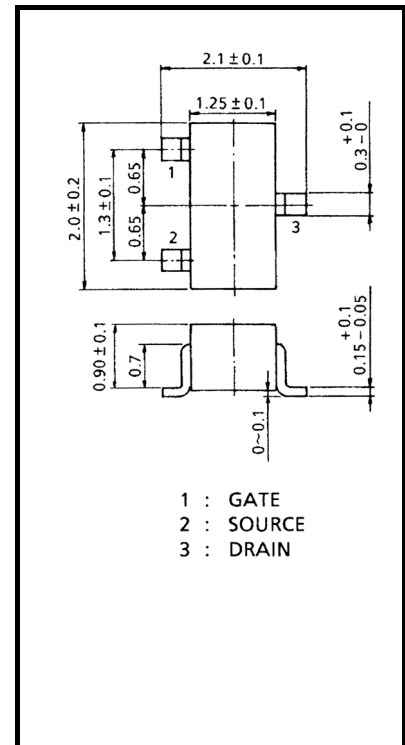
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the TY Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: mounted on FR4 board
 (25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 0.6mm² × 3)

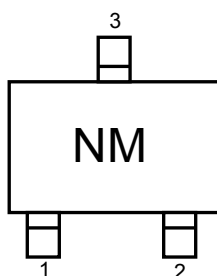


Unit: mm

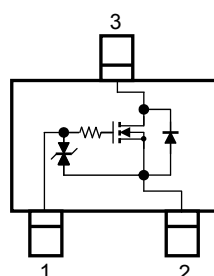


Weight: 6.0 mg (typ.)

Marking



Equivalent Circuit (top view)



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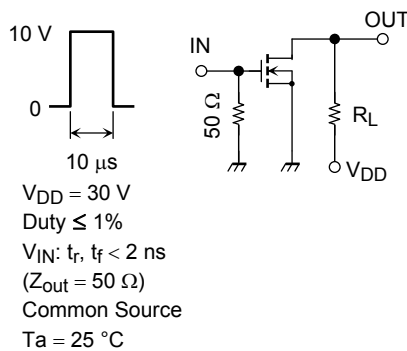
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	60	—	—	V
	$V_{(BR)DSX}$	$I_D = 10\text{ mA}, V_{GS} = -10\text{ V}$	45	—	—	V
Drain cutoff current	I_{DSS}	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	—	—	1	μA
Gate threshold voltage	V_{th}	$V_{DS} = 10\text{ V}, I_D = 0.25\text{ mA}$	1.5	—	3.1	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 200\text{ mA}$ (Note 2)	225	—	—	mS
Drain-source ON-resistance	$R_{DS(ON)}$	$I_D = 500\text{ mA}, V_{GS} = 10\text{ V}$ (Note 2)	—	1.62	2.1	Ω
		$I_D = 100\text{ mA}, V_{GS} = 5\text{ V}$ (Note 2)	—	1.90	2.6	
		$I_D = 100\text{ mA}, V_{GS} = 4.5\text{ V}$ (Note 2)	—	2.10	3.3	
Input capacitance	C_{iss}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	17.0	—	pF
Reverse transfer capacitance	C_{rss}		—	1.9	—	
Output capacitance	C_{oss}		—	3.6	—	
Switching time	Turn-on delay time	$V_{DD} = 30\text{ V}, I_D = 200\text{ mA}, V_{GS} = 0\text{ to }10\text{ V}$	—	3.3	6.6	ns
	Turn-off delay time		—	14.5	40	
Drain-source forward voltage	V_{DSF}	$I_D = -200\text{ mA}, V_{GS} = 0\text{ V}$ (Note 2)	—	-0.84	-1.2	V

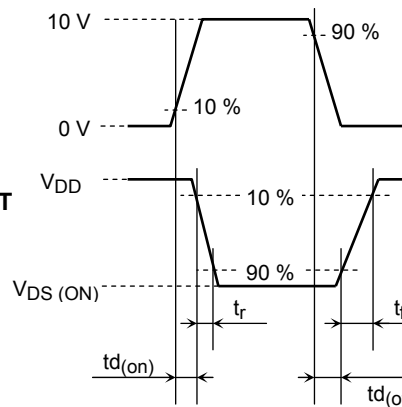
Note2: Pulse test

Switching Time Test Circuit

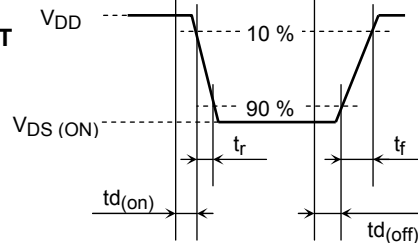
(a) Test circuit



(b) V_{IN}



(c) V_{OUT}



Precaution

Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to be low (0.25 mA for the SSM3K7002BFU). Then, for normal switching operation, $V_{GS(on)}$ must be higher than V_{th} , and $V_{GS(off)}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(off)} < V_{th} < V_{GS(on)}$.

Take this into consideration when using the device

Handling Precaution

When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.